



TM100N04D

N-Channel Enhancement Mosfet

General Description

- Low $R_{DS(ON)}$
- RoHS and Halogen-Free Compliant

Applications

- Load switch
- PWM

General Features

$V_{DS} = 40V$ $I_D = 100A$

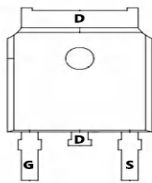
$R_{DS(ON)} = 3.8 m\Omega$ (Typ.) @ $V_{GS} = 10V$

100% UIS Tested

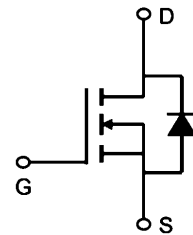
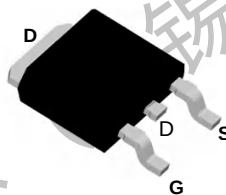
100% R_g Tested



D:TO-252-3L



Marking: 100N04



Absolute Maximum Ratings ($T_C = 25^\circ C$ Unless Otherwise Noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	100	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	55	A
I_{DM}	Pulsed Drain Current ²	240	A
EAS	Single Pulse Avalanche Energy ³	156	mJ
$P_D @ T_C = 25^\circ C$	Total Power Dissipation ³	142	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	6.6	$^\circ C/W$



TM100N04D

N-Channel Enhancement Mosfet

Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
V(BR)DSS	Drain-Source Breakdown Voltage	I _D = 250μA, V _{GS} = 0V	40	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 40V, V _{GS} = 0V	-	-	1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	1.2	1.6	2.0	V
R _{DS(ON)}	Static Drain-Source ON-Resistance ⁽⁴⁾	V _{GS} = 10V, I _D = 30A	-	3.8	5.1	mΩ
		V _{GS} = 4.5V, I _D = 20A	-	5.2	6.9	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{GS} = 0V, V _{DS} = 20V, f = 1MHz	-	3278	-	pF
C _{oss}	Output Capacitance		-	267	-	pF
C _{rss}	Reverse Transfer Capacitance		-	224	-	pF
Q _g	Total Gate Charge	V _{GS} = 0 to 10V V _{DS} = 20V, I _D = 30A	-	73	-	nC
Q _{gs}	Gate Source Charge		-	15	-	nC
Q _{gd}	Gate Drain("Miller") Charge		-	16	-	nC
Switching Characteristics						
t _{d(on)}	Turn-On DelayTime	V _{GS} = 10V, V _{DD} = 20V I _D = 30A, R _{GEN} = 3Ω	-	12	-	ns
t _r	Turn-On Rise Time		-	29	-	ns
t _{d(off)}	Turn-Off DelayTime		-	60	-	ns
t _f	Turn-Off Fall Time		-	16	-	ns
Drain-Source Diode Characteristics and Max Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	100	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	320	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S = 30A	-	-	1.2	V
t _{rr}	Body Diode Reverse Recovery Time	I _F = 20A, di/dt = 100A/us	-	16	-	ns
Q _{rr}	Body Diode Reverse Recovery Charge		-	10	-	nC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. EAS condition: Starting T_J=25C, V_{DD}=20V, V_G=10V, R_G=25ohm, L=0.5mH, I_{AS}=25A
 3. R_{θJA} is measured with the device mounted on a 1inch² pad of 2oz copper FR4 PCB
 4. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%.



TM100N04D

N-Channel Enhancement Mosfet

Typical Performance

Figure1:OutputCharacteristics

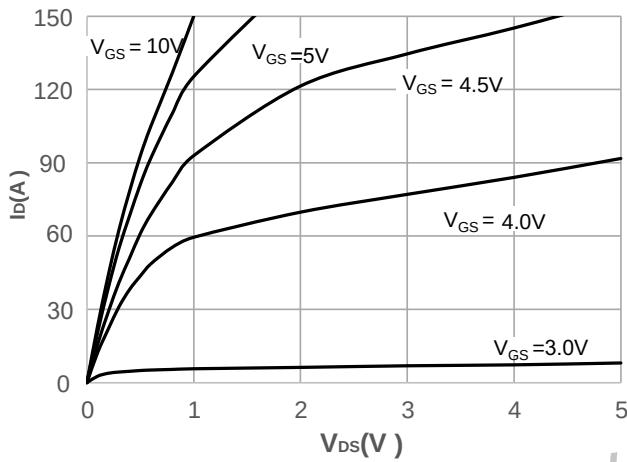


Figure 2: Typical Transfer Characteristics

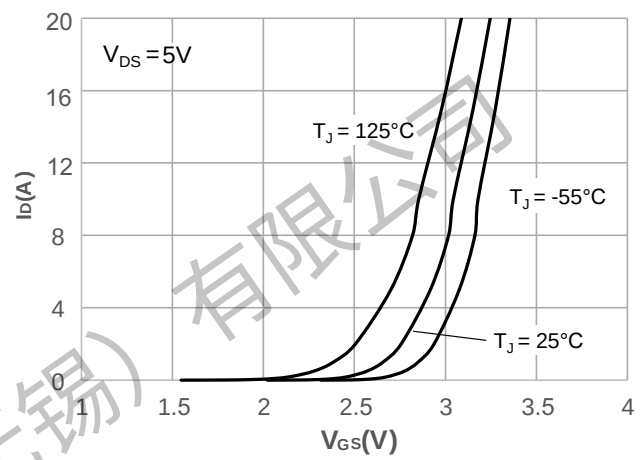


Figure 3: On-resistance vs. Drain Current

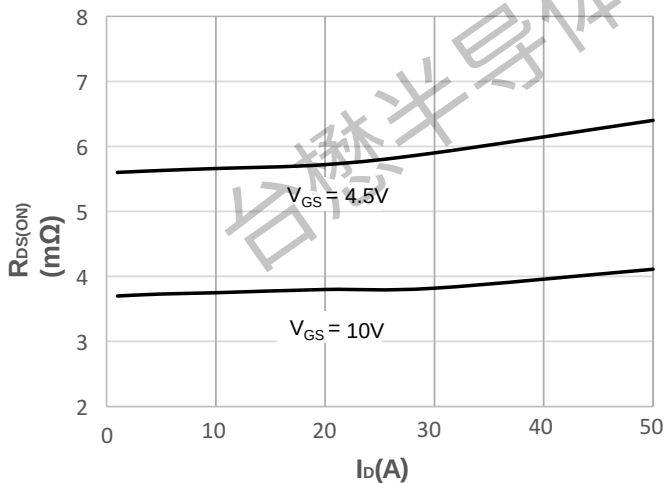


Figure 4: Body Diode Characteristics

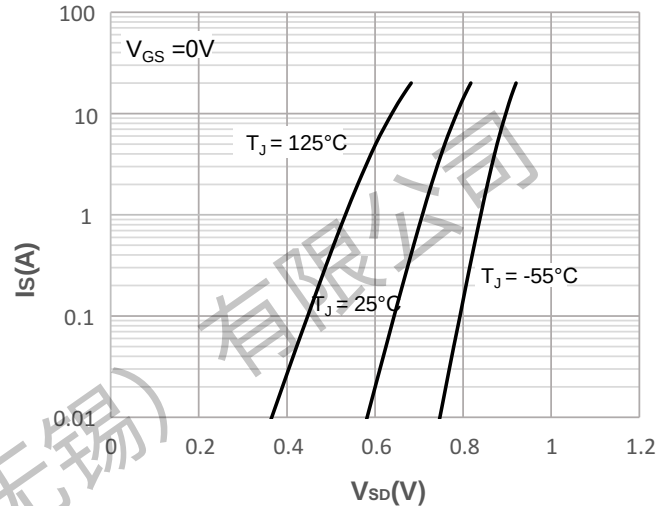


Figure 5: Gate Charge Characteristics

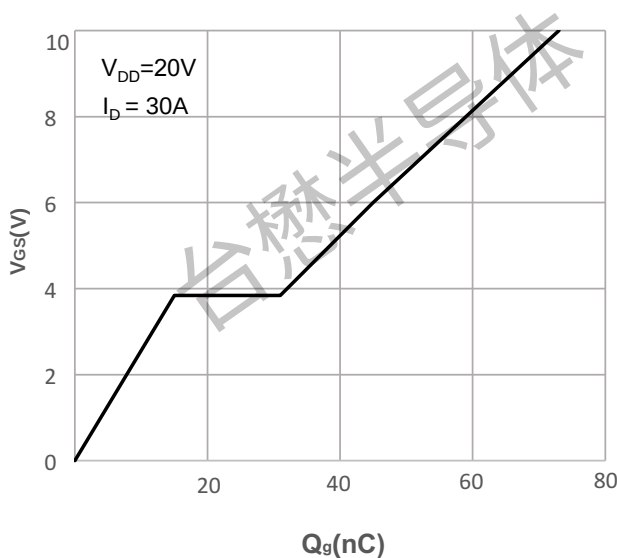
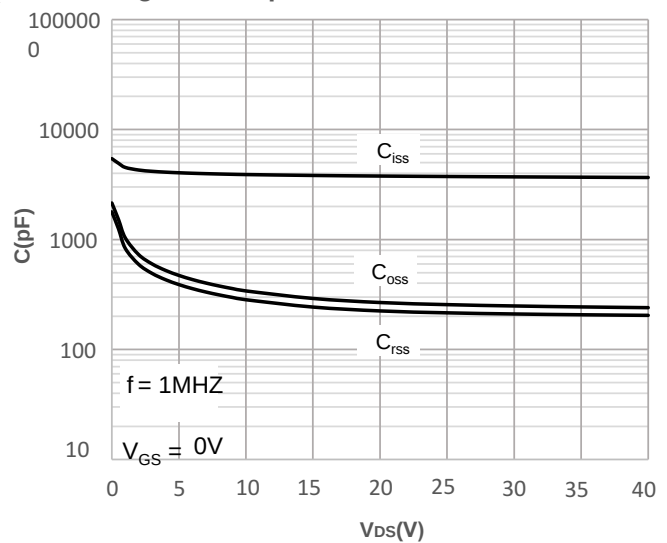


Figure 6: Capacitance Characteristics





TM100N04D

N-Channel Enhancement Mosfet

Figure 7: Normalized Breakdown voltage vs. Junction Temperature

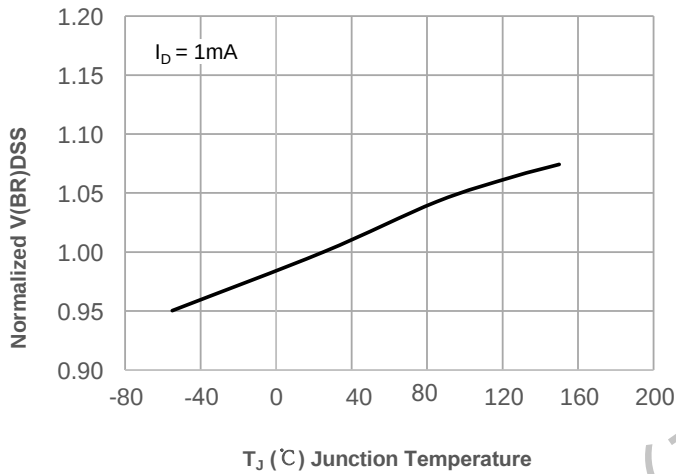


Figure 8: Normalized on Resistance vs. Junction Temperature

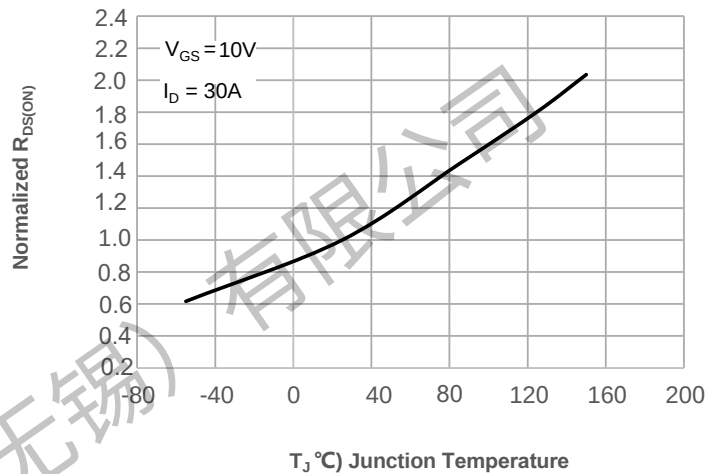


Figure 9: Maximum Safe Operating Area

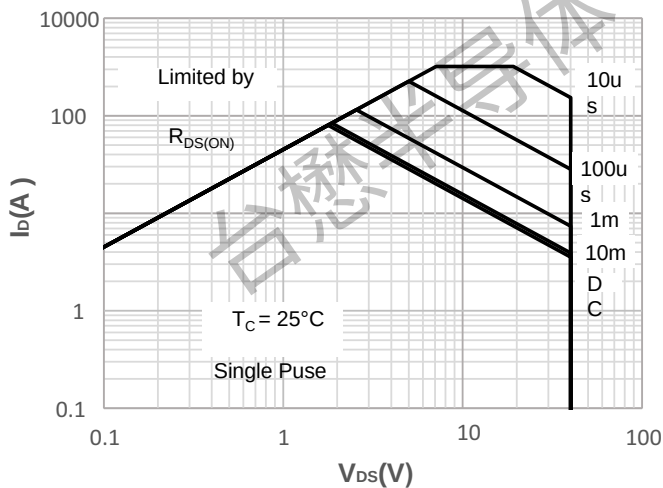


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

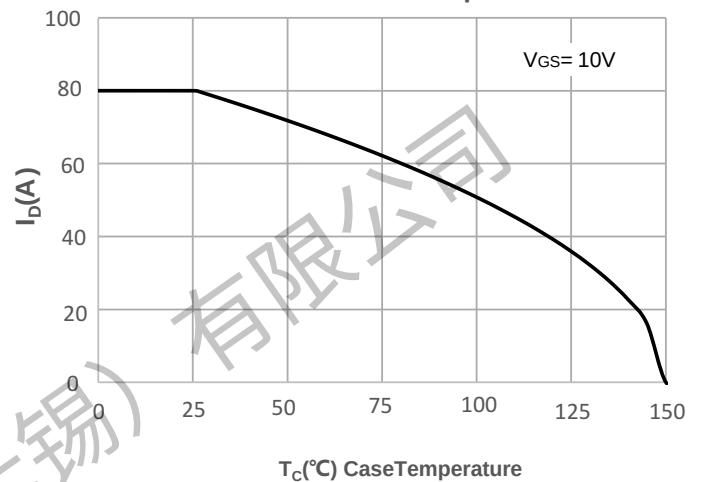


Figure 11: Normalized Maximum Transient Thermal Impedance

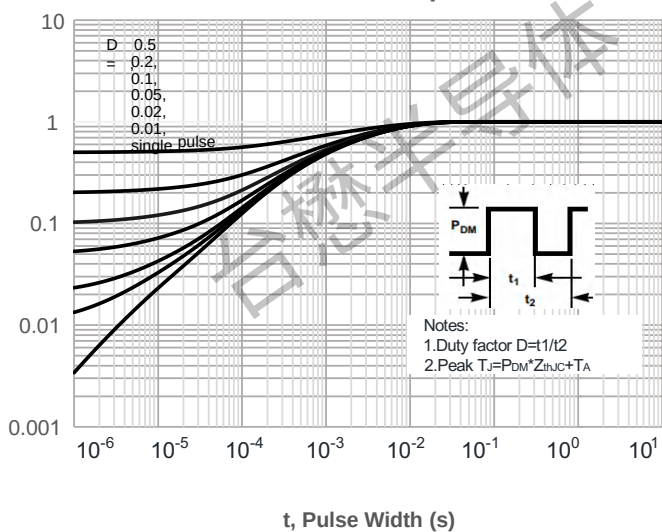
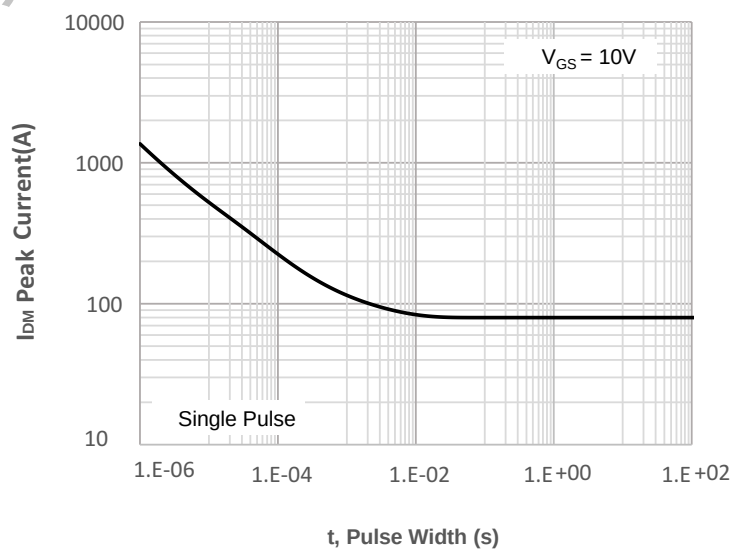


Figure 12: Peak Current Capacity

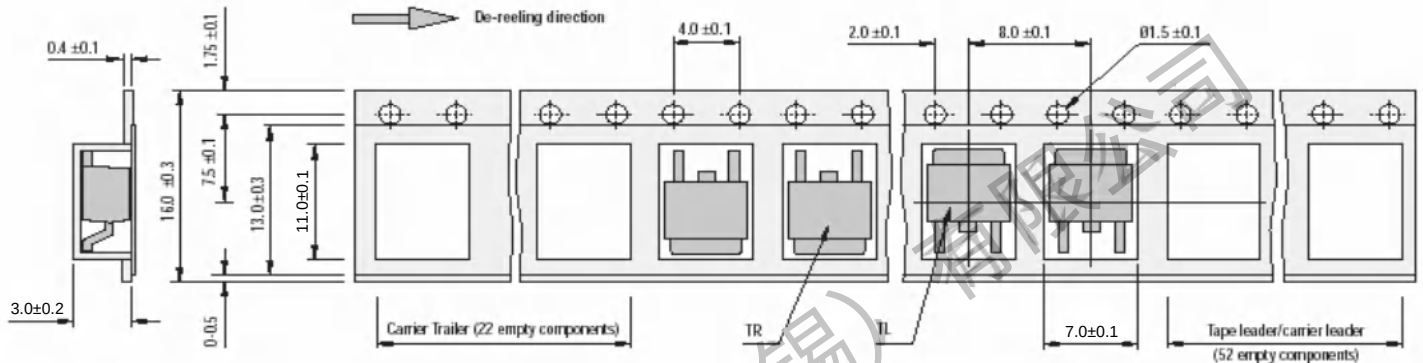




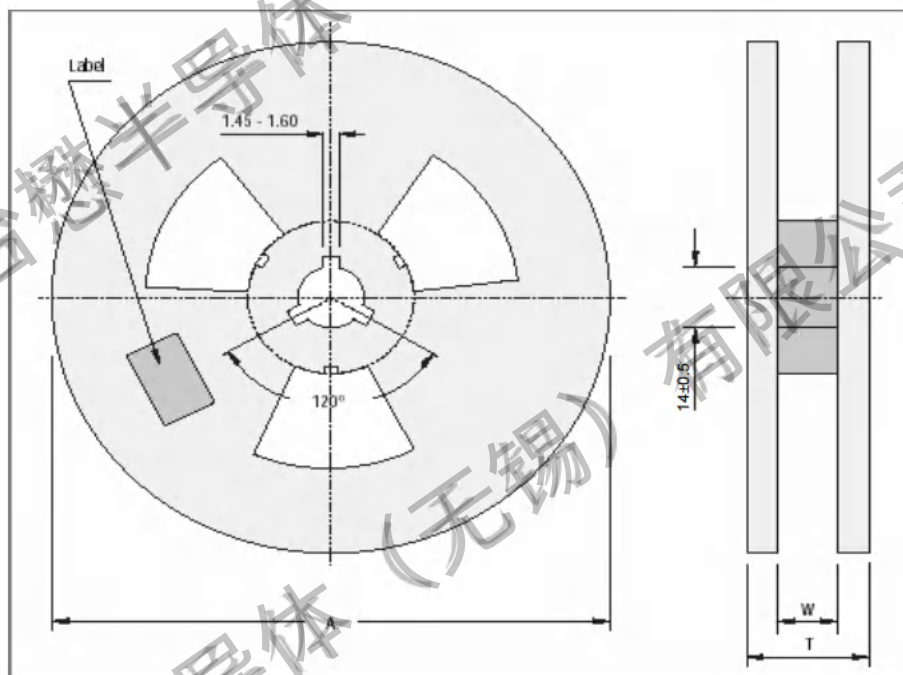
TM100N04D

N-Channel Enhancement Mosfet

TO-252-3L Embossed Carrier Tape



TO-252-3L Reel



All Dimensions are in mm.

Reel Specifications				
Package	Tape Width	Reel Dia. A - Max	Inside Thickness W	Reel Thickness T - max
TO-252-3L	16	330	18.0 ± 1.5	20

Packaging Information

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
2,500 pcs	13 inch	5,000 pcs	355×370×50	25,000 pcs	380×275×380	

Important Notices and Disclaimers

- Tritech-MOS Technology Corp. reserves the right to change this document, its products, and specifications at any time without prior notice.
- Before final design, purchase, or use, customers should obtain and confirm the latest product information and specifications.
- Tritech-MOS Technology Corp. makes no warranties, representations or warranties regarding the suitability of its products for any specific purpose, and Tritech-MOS Technology Corp. does not assume any responsibility for application assistance or customer product design.
- Tritech-MOS Technology Corp. does not guarantee or assume any responsibility for the purchase or use of any unexpected or unauthorized products.
- Any intellectual property rights of Tritech-MOS Technology Corp. are not licensed through implicate or other means.
- Products of Tritech-MOS Technology Corp. are not included as critical components in life support equipment or systems without explicit written approval from Tritech-MOS Technology Corp.

Revision history:

Date	Rev	Description	Page
2023.08.03	23.08	Original	